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ABSTRACT

An electronic device material comprising at least an electronic device substrate and a silicon oxynitride film disposed on the substrate is provided. The silicon oxynitride film is characterized by containing nitrogen atoms in a large amount in the vicinity of the oxynitride film surface when the nitrogen content distribution in the thickness direction of the silicon oxynitride film is examined by SIMS (secondary ion mass spectrometry) analysis. By virtue of this constitution, an electronic device material comprising an oxynitride film having an excellent effect of preventing penetration of boron and having excellent gate leak properties can be obtained.